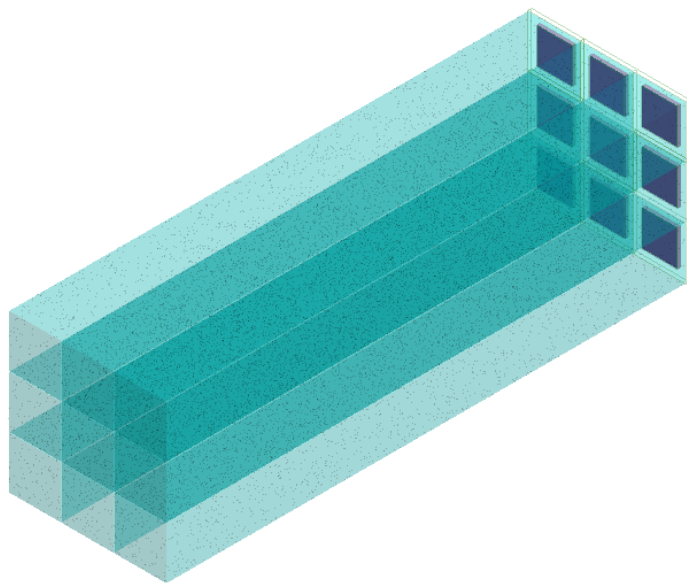


Geant4 Standalone Optical simulation studies of S14160-6010PS/6015PS MPPC's



Used Code from:

<https://github.com/JeffersonLab/glass-prototype>

Author: Petr Stepanov

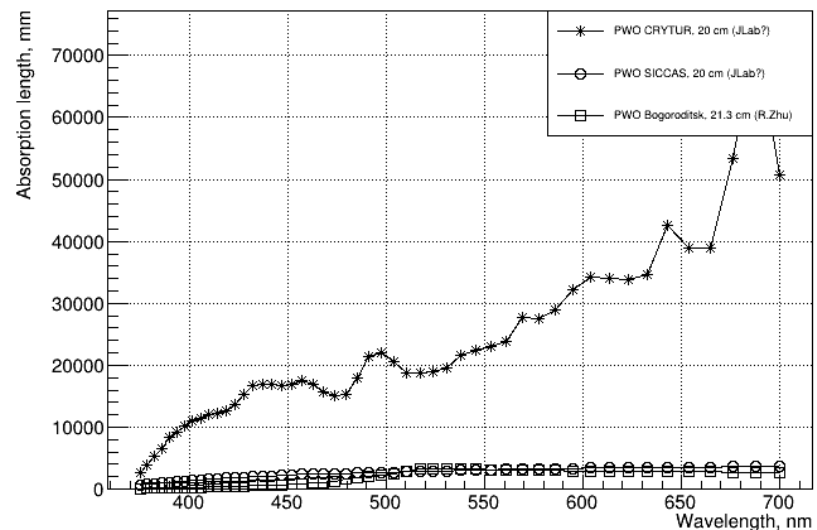
Provided by: Dmitry Kalinkin

Simulation Setup

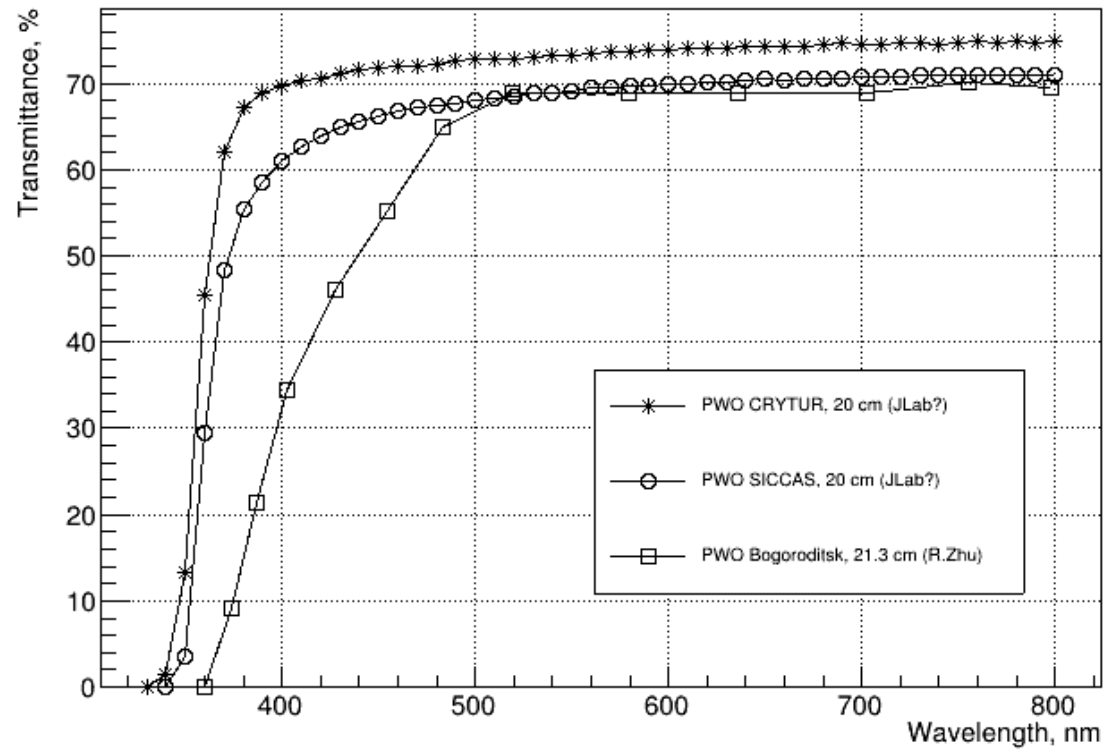
- Material – PWO-CRYTUR
- Matrix – 3x3,5x5
- Wrap material – VM2000
- Physics List – FTFP_BERT

- 1Mev – 300 Op. Photons
- Single particle simulations
- Particle - e-
- Finish model – dielectric-metal
- Finish type - unified

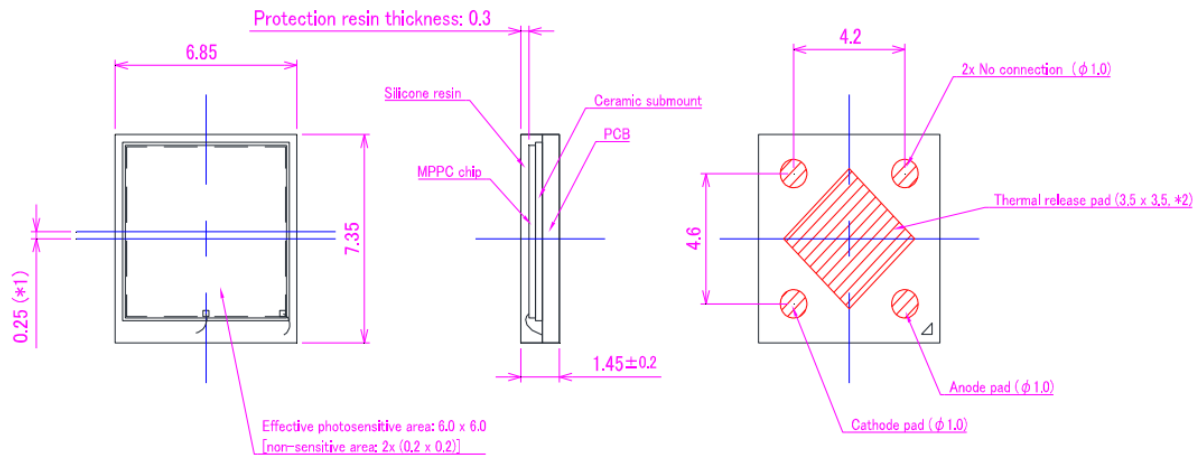
Calculated PWO Absorption Length



PWO Transmittance Spectra



S14160-6010PS/6015PS properties



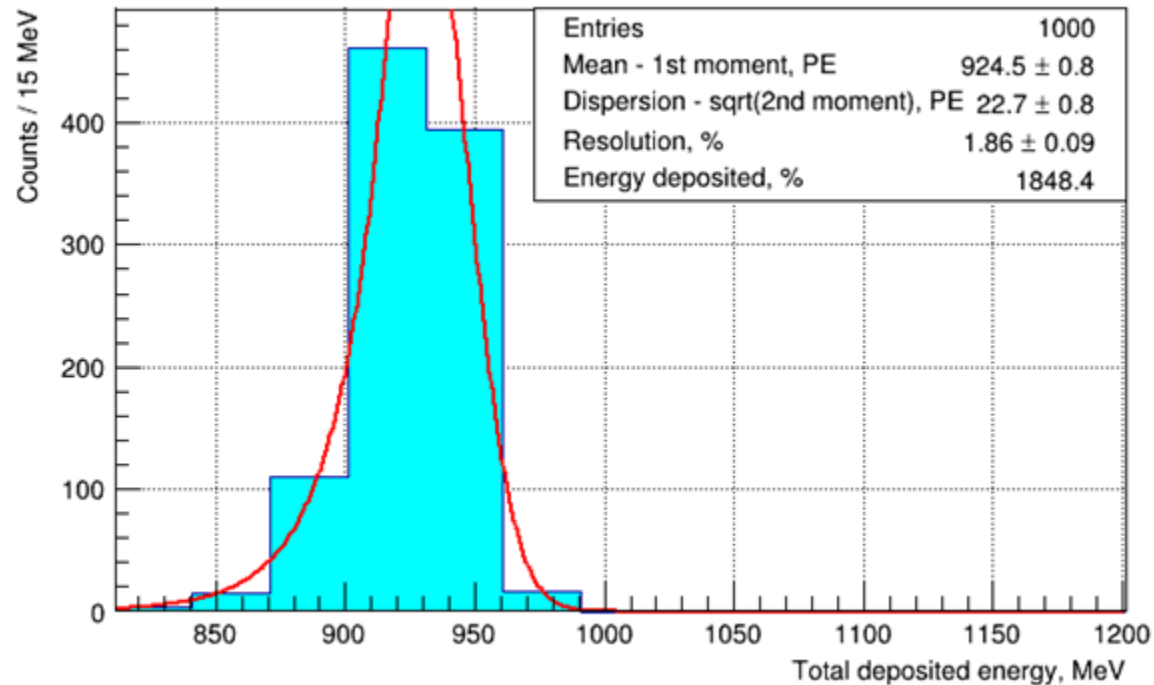
*1 : Chip center to PKG center

*2 : The thermal pad is not electrically but thermally connected to MPPC chip.
It is recommended that the pad is connected to ground plane for thermal release.

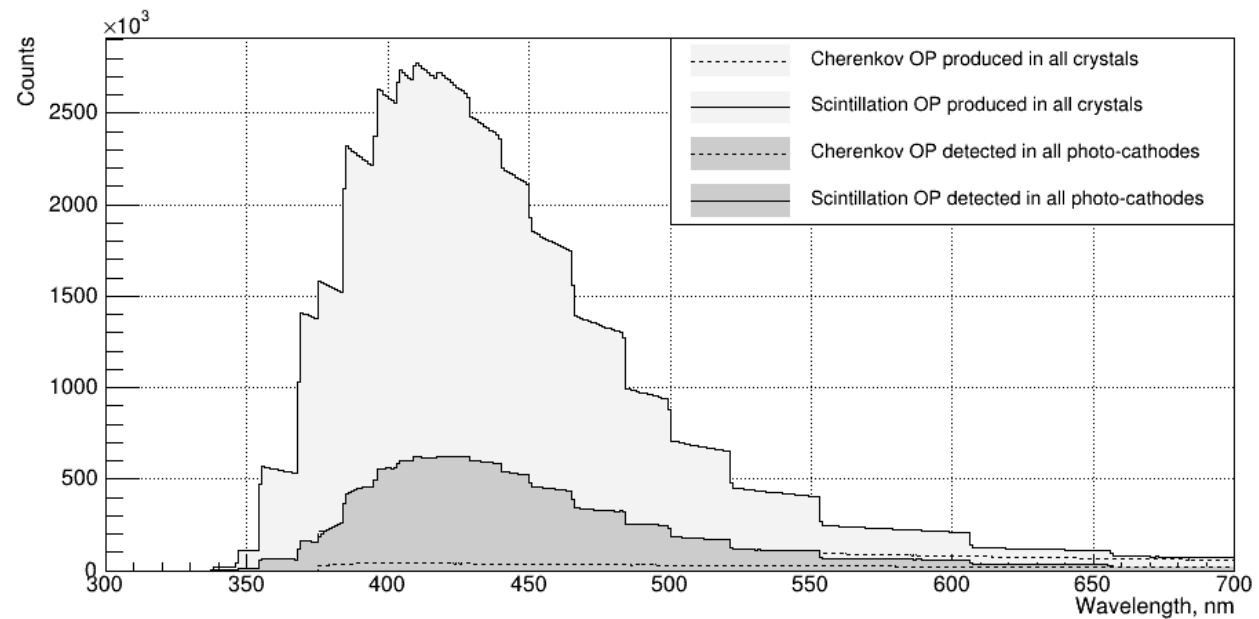
General tolerance : ±0.1

Instead of 4 siPM's with size 6.85mm*7.35mm on one crystal. One siPM with size 13mm² were used.

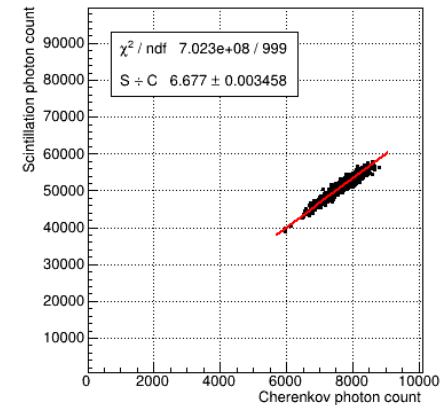
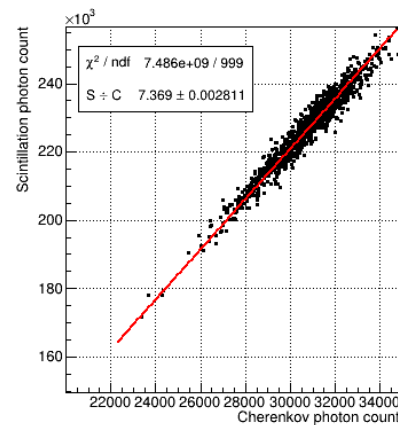
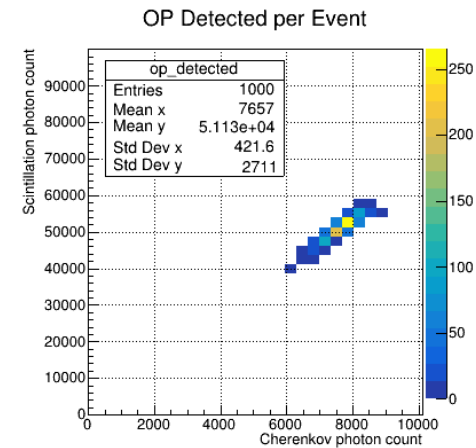
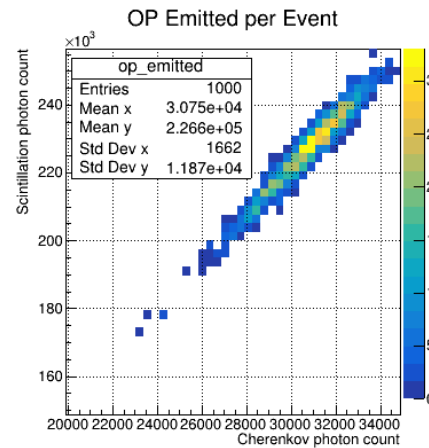
Energy Deposition 1000 events, 3x3 Matrix, 1Gev



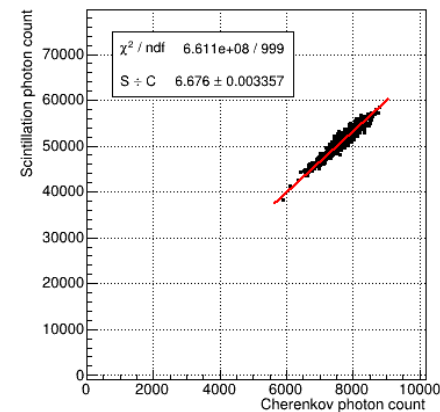
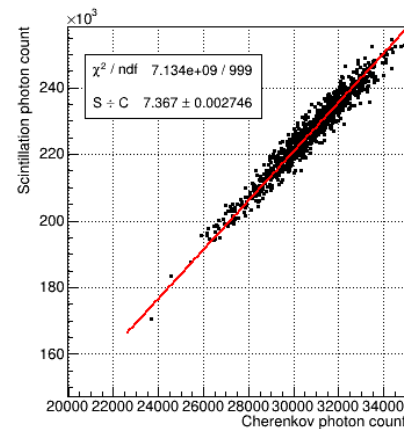
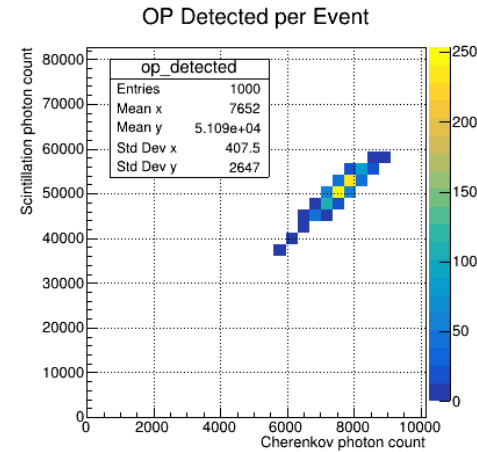
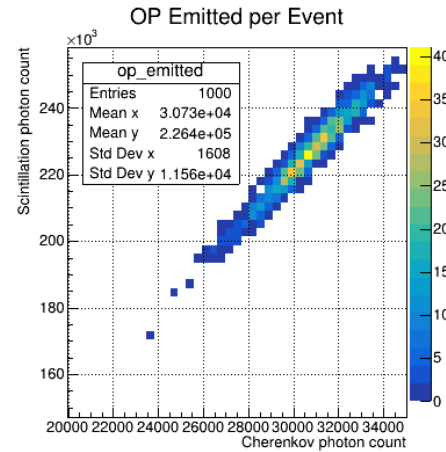
Emitted vs Detected Scintillation and Cherenkov OP Spectra 1000 events, 3x3 Matrix, 1Gev



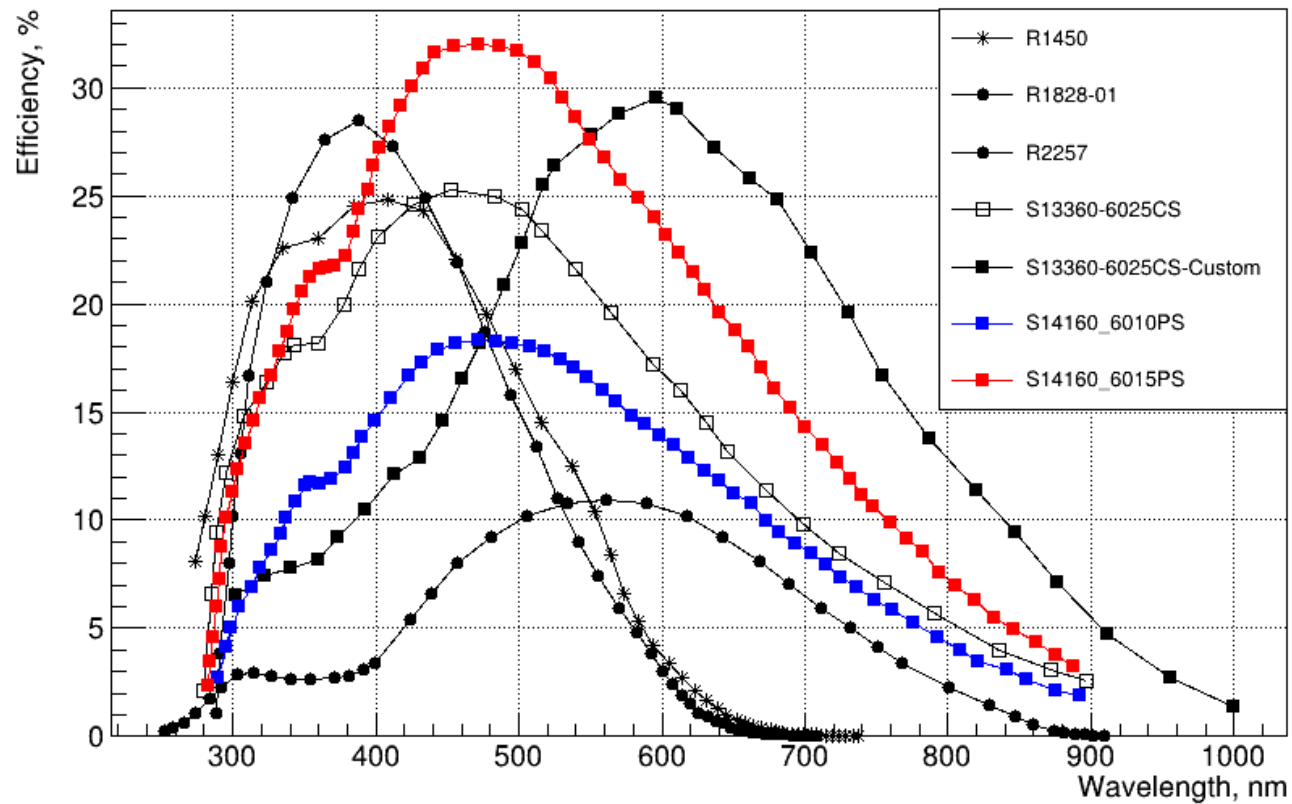
Cerenkov vs Scintillation distributions, for 3x3, 1000 events, 1GeV for S14160-6010PS



Cerenkov vs Scintillation distributions, for 3x3, 1000 events, 1GeV for S14160-6015PS

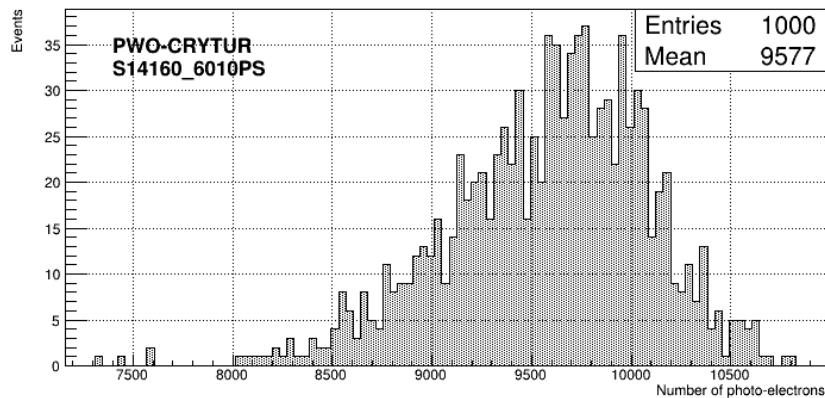


Detector Quantum efficiencies

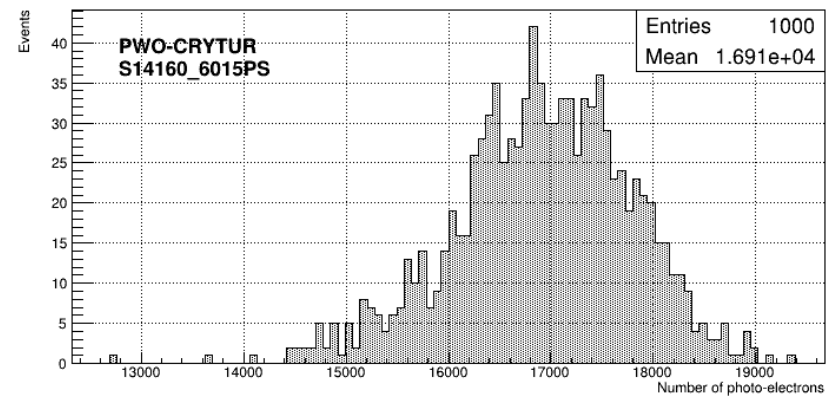


Comparison of number of photo-electrons for different reflector model and finish types for 3x3, 1000 events, 1GeV

Number of Photo-electrons S14160-6010PS



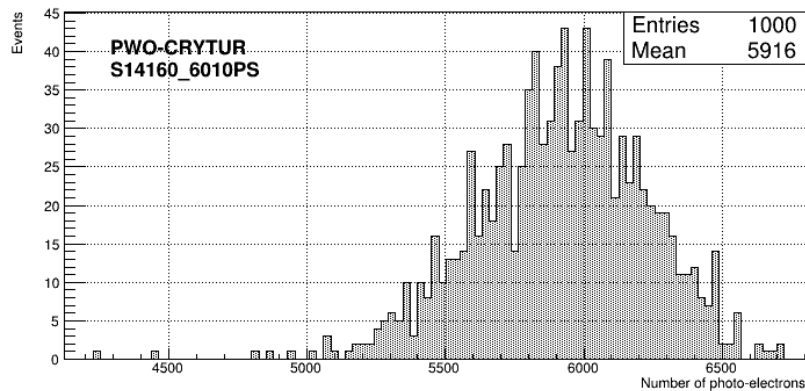
Number of Photo-electrons S14160-6015PS



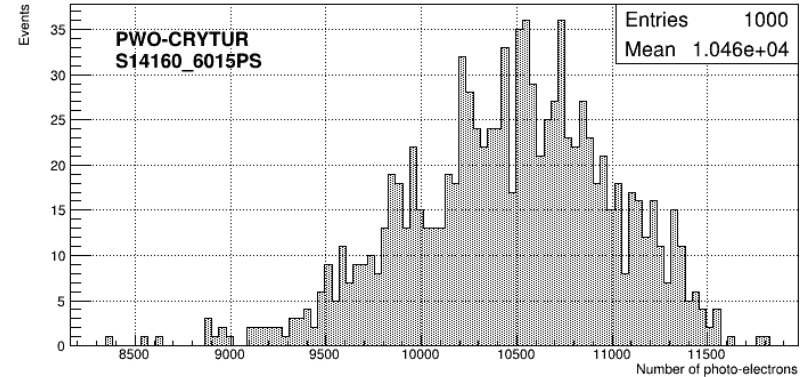
- Finish model – dielectric-metal
- Finish type - unified

Comparison of number of photo-electrons for different reflector model and finish types for 3x3, 1000 events, 1GeV

Number of Photo-electrons S14160-6010PS



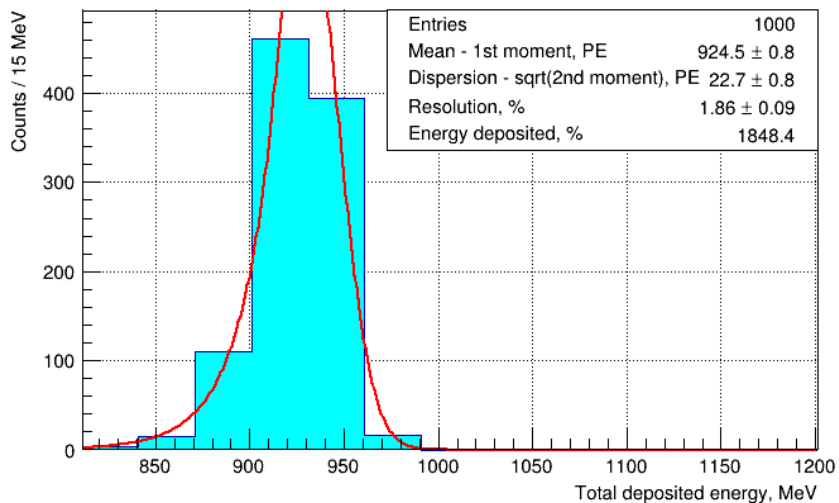
Number of Photo-electrons S14160-6015PS



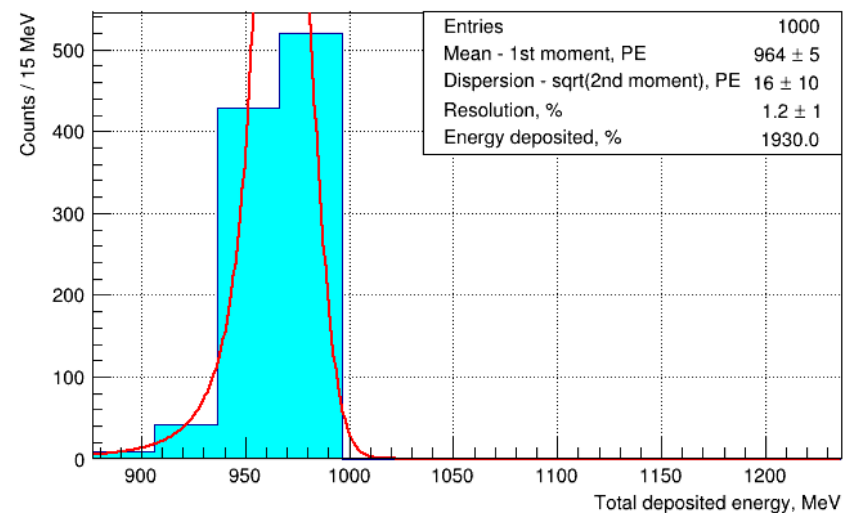
- Finish model – dielectric-LUT
- Finish type - LUT

Comparison of deposited energies for 3x3 and 5x5 crystal configurations 1000 events, 1 GeV, S14160-6015PS

3X3

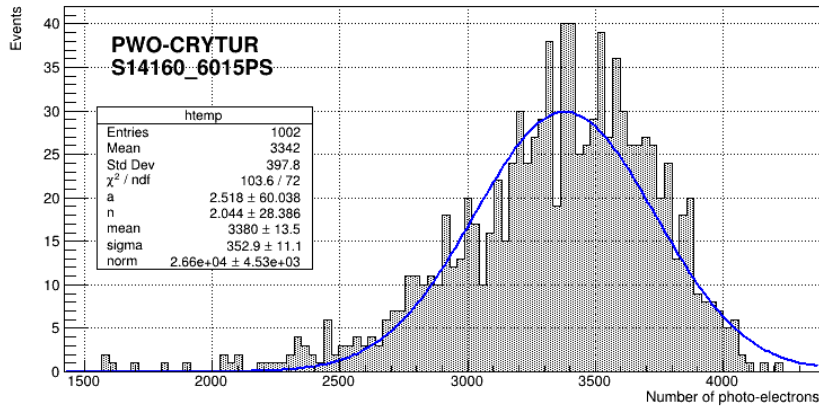


5X5

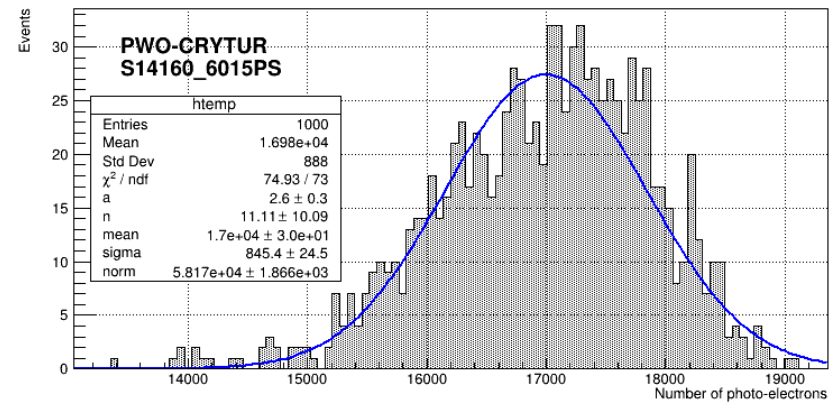


Number of photo-electrons for different
incident electron momentum, 5x5 crystal configuration,
all cells included

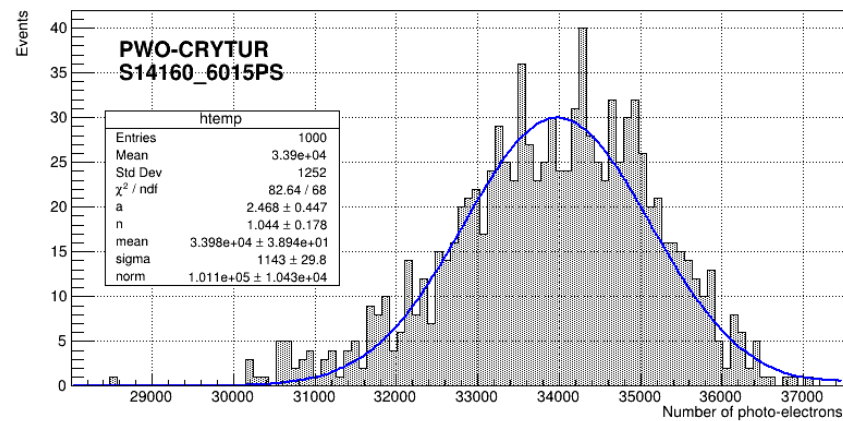
200 Mev



1 Gev

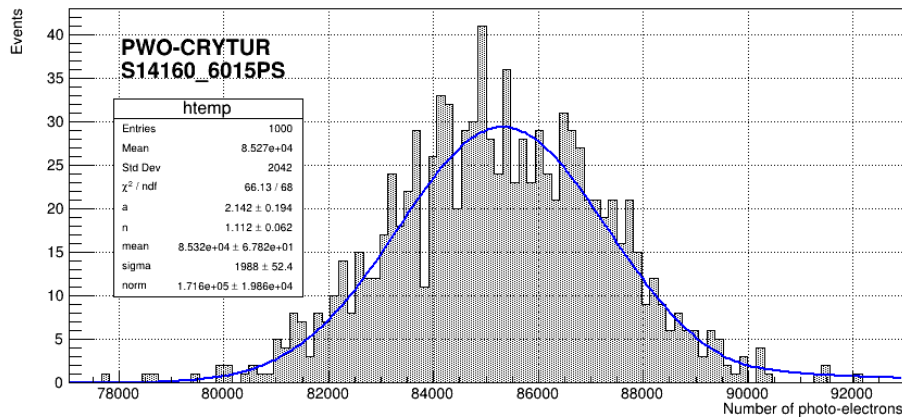


2 Gev

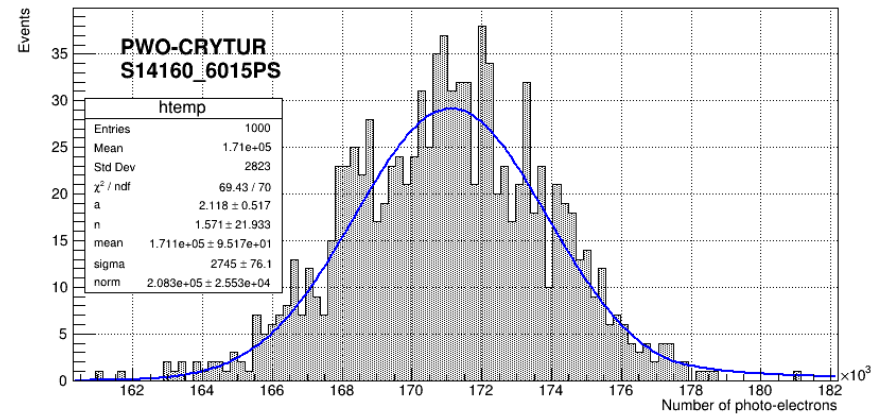


Number of photo-electrons for different
incident electron momentum,
5x5 crystal configuration, all cells included

5 Gev



10 Gev



Number of photons that reach the sensors per unit of energy deposited as a function of incident electron momentum, all cells included

